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Surface electronic structure and isotropic superconducting gap in (Li_{0.8}Fe_{0.2})OHFeSe

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Using angle-resolved photoemission spectroscopy (ARPES), we revealed the surface electronic structure and superconducting gap of ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OHFeSe, an intercalated FeSe-derived superconductor without antiferromagnetic phase or Fe-vacancy order in the FeSe layers, and with a superconducting transition temperature (T_c) ~ 40 K. We found that ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OH layers dope electrons into FeSe layers. The electronic structure of surface FeSe layers in ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OHFeSe resembles that of Rb_xFe_{2-y}Se₂ except that it only contains half of the carriers due to the polar surface, suggesting similar quasiparticle dynamics between bulk ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OHFeSe and Rb_xFe_{2-y}Se₂. Superconducting gap is clearly observed below T_c , with an isotropic distribution around the electron Fermi surface. Compared with $A_x\text{Fe}_{2-y}\text{Se}_2$ (A=K, Rb, Cs, Tl/K), the higher T_c in ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OHFeSe might be attributed to higher homogeneity of FeSe layers or to some unknown roles played by the ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OH layers.

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Heavily electron-doped iron selenide superconductors (HEDIS), such as $A_x \text{Fe}_{2-y} \text{Se}_2$ (A=K, Rb, Cs, Tl/K) [1, 2] and single-layer FeSe on oxides (SrTiO₃, BaTiO₃) [3–8], are currently the research focus in the field of iron-based superconductors. The absence of hole Fermi surfaces [9], together with the nodeless superconducting gap [7, 9] in these materials pose great challenges on various pairing theories [10]. Moreover, the dominant factors that induce high T_c remains perplexing. In single-layer FeSe, evidence of record high T_c of iron-based superconductors has been observed [3–8, 11]. It is proposed that the interaction with the interfacial oxide would significantly enhance the T_c of FeSe [8, 12]. However, the air sensitivity of the FeSe films induces difficulties in systematic ex-situ characterizations, and thus the relationship between T_c and interfacial interactions remains unsettled. In A_x Fe_{2-y}Se₂, there is an intrinsic mesoscopic phase separation of a superconducting phase and an Fe-vacancy ordered antiferromagnetc insulating phase [13-17]. It is argued that the mesoscopic coexistence with the Fe-vacancy ordered phase K₂Fe₄Se₅ could give rise to superconductivity in KFe₂Se₂ [18]. However, the phase separation makes it intricate to experimentally determine the intrinsic nature of the superconducting phase. It is crucial to study more HEDIS materials, especially those with decent stability in air and without phase separation, for understanding the pairing symmetry and high T_c in HEDIS.

Recently, a new intercalated FeSe-derived superconductor with T_c higher than 40 K, (Li_{0.8}Fe_{0.2})OHFeSe, has been synthesized [19]. The crystal structure consists of alternating stacking layers of FeSe and (Li_{0.8}Fe_{0.2})OH [Fig. 1(a)]. Based on the chemical formula, there are 0.2 electrons per formula unit in the (Li_{0.8}Fe_{0.2})OH layer, which could be transferred to the FeSe layer, making this material a new HEDIS candidate,

while experiments on its electronic structure are still lacking. Moreover, this material shows a good stability in air, and its single crystals can be grown readily with size of millimeters [20]. In particular, there is no Fe-vacancy ordered phase or antiferromagnetism in the FeSe layers, which makes this material a promising prototype for studying the superconductivity of HEDIS.

Using angle-resolved photoemission spectroscopy (ARPES), we studied the surface electronic structure of (Li_{0.8}Fe_{0.2})OHFeSe. We found that the Fermi surface consists of only electron pockets. The top FeSe layer probed by ARPES shows a carrier concentration of $0.1e^-$ per Fe, which should be half of the bulk doping level considering the polar discontinuity at the topmost FeSe layer, confirming that (Li_{0.8}Fe_{0.2})OHFeSe is an HEDIS material. isotropic superconducting gap has been observed around the electron pockets. Considering the chemical potential shift by the additional doping in bulk, our data suggest that the electronic structure and quasiparticle dynamics in (Li_{0.8}Fe_{0.2})OHFeSe are similar to those in A_x Fe_{2- ν}Se₂. Comparing (Li_{0.8}Fe_{0.2})OHFeSe with Rb_{0.76}Fe_{1.87}Se₂, we argue that the crystalline homogeneity of FeSe layers and some unknown effects of (Li_{0.8}Fe_{0.2})OH layers in (Li_{0.8}Fe_{0.2})OHFeSe could be the key factors that promote its higher T_c .

Single crystals were grown using the method as described in ref. [19, 20]. Fig. 1(b) shows the magnetic susceptibility measurement on a typical (Li_{0.8}Fe_{0.2})OHFeSe sample, indicating that the superconductivity occurs at $T_c \sim 40$ K. High-resolution ARPES measurements were performed at the I05 beamline of the Diamond Light Source and our in-house ARPES system with a Helium discharged lamp (21.2 eV photons), using Scienta R4000 electron analyzers. The overall energy resolution was $5\sim12$ meV, and the angular resolution was

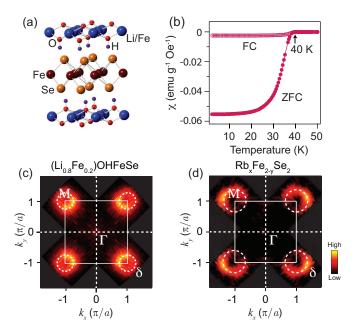


FIG. 1: (a)The crystal structure and (b) magnetic susceptibility of (Li_{0.8}Fe_{0.2})OHFeSe. (c, d) False color plots of the photoemission intensity maps at the Fermi energy (E_F) of $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$ and Rb_{0.76}Fe_{1.87}Se₂ respectively. The intensity was integrated over an energy window of $(E_F-15 \text{ meV}, E_F+15 \text{ meV})$. The Fermi surface maps are four-fold symmetrized plotted over the projected two-dimensional Brillouin zone for the unit cell of two iron ions. The Fermi surfaces of the δ band are shown by the dashed circles. In this figure and hereafter, the data of (Li_{0.8}Fe_{0.2})OHFeSe and Rb_{0.76}Fe_{1.87}Se₂ were taken with 21.2 eV photons from an in-house helium discharge lamp and 64 eV photons at Beamline I05 of Diamond Light Source, respectively. Taking the inner potential of 11 eV [9] to calculate the k_z 's of Rb_{0.76}Fe_{1.87}Se₂, we measured at the Γ -M plane of Rb_{0.76}Fe_{1.87}Se₂. The Fermi surface of (Li_{0.8}Fe_{0.2})OHFeSe shows negligible k_z dependence in photon-energy-dependent ARPES study. The data were taken at T < 15 K.

0.3 degrees. All samples were cleaved *in-situ* under ultra-high vacuum conditions. During measurements, the spectroscopy qualities were carefully monitored to avoid the sample aging issue.

The single crystals of $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$ can be easily cleaved along the interface between $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OH}$ layers and FeSe layers due to the weak hydrogen bonding interaction between them [19]. Patches of both $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OH}$ and FeSe exist on the exposed surface after cleavage, which has been confirmed by our STM measurements [21]. Figure 1(c) is the photoemission intensity map at Fermi energy (E_F) taken using photon energy of 21.2 eV, and negligible k_z dependence of Fermi surface has been confirmed by our photon-energy-dependent ARPES study. The Fermi surface of $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$ consists of electron pockets around the zone corner M and negligible spectral weight at the zone center Γ . This Fermi surface topology is identical to that of $A_x\text{Fe}_{2-y}\text{Se}_2$ at Γ -M plane, as exemplified by the photoemission intensity map at E_F in Rb_{0.76}Fe_{1.87}Se₂ shown in

Fig. 1(d). Quantitatively, the size of the electron pockets is much smaller in ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OHFeSe than in Rb_{0.76}Fe_{1.87}Se₂. Based on the Luttinger volume, the estimated carrier concentration is 0.1 electrons per Fe in ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OHFeSe, while that of Rb_{0.76}Fe_{1.87}Se₂ is 0.2 electrons per Fe, considering the degenerated δ and δ ' electron pockets at E_F . We note that both FeSe and ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OH layers are metallic based on our STM results [21], and thus they could both contribute to the spectral weight in ARPES measurements. Nevertheless, our data show the spectral weight only from the FeSe layer, without evident components from ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OH. One possible reason is that the matrix element of the ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OH states is much weaker than that of the FeSe states in our experimental setup.

Due to the surface-sensitive characteristic of ARPES, what we actually measured is the surface electronic structure of (Li_{0.8}Fe_{0.2})OHFeSe, which should be different from the bulk case because of the polar discontinuity at the surface. The top FeSe layer has only one adjacent charge reservoir layer of (Li_{0.8}Fe_{0.2})OH, and compared with the FeSe layers in the bulk, it retains only half of the doped charges based on simple polar analysis [22]. Nevertheless, with the preserved in-plane structure parameter/bond length, the variation of electron carriers on the top FeSe layer would mostly affect the chemical potential other than the band structure or the electron correlation, as demonstrated in $Ba_{1-x}K_xFe_2As_2$ with different K doping [23]. Based on this, we argue that the bulk Fermi surface of (Li_{0.8}Fe_{0.2})OHFeSe could be similar to that in Rb_{0.76}Fe_{1.87}Se₂, in both topology and pocket size, and the surface electronic structure measured by ARPES could to some extent reveal the quasiparticle dynamics and electron correlation of bulk (Li_{0.8}Fe_{0.2})OHFeSe.

The surface band dispersions of (Li_{0.8}Fe_{0.2})OHFeSe are shown in Fig. 2. Figures 2 (a),(c) show the photoemission intensity along the cut #1 together with the secondderivative images for (Li_{0.8}Fe_{0.2})OHFeSe and Rb_{0.76}Fe_{1.87}Se₂, respectively. The corresponding energy distribution curves (EDCs) are plotted in Figs. 2 (b),(d). The band structures of (Li_{0.8}Fe_{0.2})OHFeSe and Rb_{0.76}Fe_{1.87}Se₂ are rather similar. We are able to resolve a dispersive β band under the E_F and an electron-like band δ around M point. Around 200 meV and 330 meV below E_F , we observe two rather flat d_{72} bands assigned as ω ' and ω respectively in (Li_{0.8}Fe_{0.2})OHFeSe, which are weak but still present in Rb_{0.76}Fe_{1.87}Se₂, and have also been resolved in the previous ARPES results on superconducting $K_x Fe_{2-y} Se_2$ [24]. In particular, the bandwidths of the β are nearly the same for these two compounds, suggesting that the band dispersions and correlation strength of (Li_{0.8}Fe_{0.2})OHFeSe is very similar to those of A_x Fe_{2- ν}Se₂. We also note that there are some spectra weight at E_F around Γ point in Rb_{0.76}Fe_{1.87}Se₂ due to the strong k_7 dispersion of κ around Z point of the Brillouin zone [9, 24], which is absent in the spectra of (Li_{0.8}Fe_{0.2})OHFeSe. This discrepancy could be accounted by the lighter electron doping in the surface layer of (Li_{0.8}Fe_{0.2})OHFeSe.

The evolution of the superconducting gap with temperature

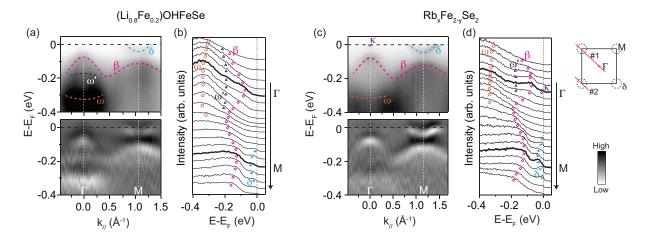


FIG. 2: (a) Photoemission intensity $I(k, \omega)$ (upper panel) of $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$ and its second derivative $[\partial_{\omega}^2 I(k, \omega)]$ (lower panel) along the Γ -M direction (cut #1) in the right inset. The data were measured at T=14 K. (b) The EDCs for the photoemission intensity in panel (a). (c), (d) Same as in panels (a), (b), but the data were taken from Rb_{0.76}Fe_{1.87}Se₂ at T=6 K.

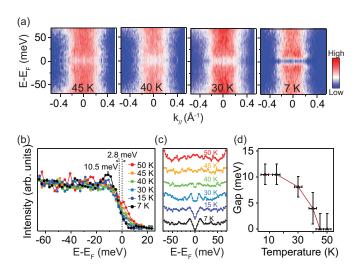


FIG. 3: (a) The symmetrized (with respect to E_F) photoemission intensity of (Li_{0.8}Fe_{0.2})OHFeSe at T=45, 40, 30, and 7 K along the cut #2 in the right inset of Fig. 2(c). At T=40, 30, and 7 K, the spectral weight suppression at k_F near E_F indicates a gap opening. (b) Temperature dependence of the spectral weight integrated over the small momentum region around k_F . (c) The spectral weight in (b) is symmetried with respect to E_F to show the variation of gap size. (d) Temperature dependence of the gap size extracted from (c).

is plotted in Fig. 3. As shown in Fig. 3(a), there is no gap at E_F near the Fermi momentum in the normal state, whereas a clear superconducting gap shows up at low temperatures in the superconducting state. With decreasing temperature, the spectra weight near the E_F is depleted and a coherent peak grows in Fig. 3(b). We identify that the value of leading edge gap is ~ 2.8 meV. Using the coherent peak position as a measurement of superconducting gap, we estimate that it is ~ 10.5 meV, very similar to the value in $A_x \text{Fe}_{2-y} \text{Se}_2$ materials [9]. In Fig. 3(c), the symmetrized EDCs with respect to E_F demonstrate the gap opening with decreasing tem-

perature. Fig. 3(d) shows the superconducting gap size as a function of temperature determined from Fig. 3(c), clearly indicating a T_c around 40 K, which is consistent with the results of the magnetic susceptibility measurements (Fig. 1(b)). By examining the superconducting gap size at various Fermi crossings of the δ band around M, we plot its momentum distribution in Fig. 4. Within the experimental uncertainties, the superconducting gap is isotropic with a size of \sim 10 meV. The gap amplitude is similar to that of A_x Fe_{2-v}Se₂ [9]. The T_c of (Li_{0.8}Fe_{0.2})OHFeSe is 30% higher than that of Rb_{0.76}Fe_{1.87}Se₂, so we naturally expect that the former has a superconducting gap greater than 10 meV. The observation of 10 meV gap size here could be due to the fact that the top FeSe surface layer is underdoped compared with the FeSe layers in the bulk. Due to the proximity effect, this underdoped surface FeSe layer shows a smaller gap value but a gap-closing temperature close to the bulk T_c . Other bulk sensitive experimental probes are required to reveal the bulk superconducting gap in (Li_{0.8}Fe_{0.2})OHFeSe.

Previously, we noted that there is an empirical correlation between the in-plane lattice constant and T_c for several heavily electron-doped FeSe-derived superconductors [6]. However, our recent systematic study of a large class of heavily electron-doped FeSe-derived bulk superconductors, including $K_xFe_{2-y}Se_{2-z}S_z$, $Rb_xFe_{2-y}Se_{2-z}Te_z$ and $(Tl,K)_xFe_{2-y}Se_{2-z}S_z$, indicates that the electronic correlation (or effective bandwidth) is more directly correlated with T_c [26]. We have shown that the electronic structure of (Li_{0.8}Fe_{0.2})OHFeSe highly resembles that of $A_x \text{Fe}_{2-y} \text{Se}_2$. Particularly, its bandwidth is also similar to that of the A_x Fe_{2- ν}Se₂, although its T_c is about 10 K higher than that of $A_x \text{Fe}_{2-y} \text{Se}_2$. This is likely due to the intact FeSe layer of the former, since the inhomogeneity and intergrowth of multiple phases in the latter might suppress superconductivity. Actually, in some $A_x \text{Fe}_{2-y} \text{Se}_2$ compounds, though the bulk superconductivity occurs around 30 K, there are signs of filamentary superconducting phase with

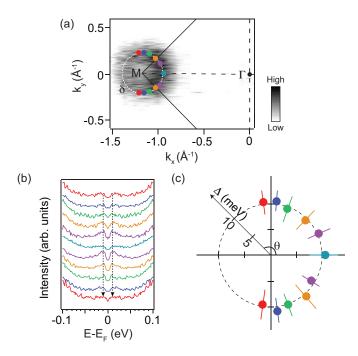


FIG. 4: (a) Photoemission intensity map of the δ band around the zone corner M. The data were integrated over an energy window of $(E_F-15 \text{ meV}, E_F+15 \text{ meV})$. (b) The symmetrized (with respect to E_F) EDCs taken at various Fermi crossings at the δ band, as indicated by the dots in (a). (c) Gap distribution of the δ band around M in polar coordinates, where the radius indicates the gap size, and the polar angle θ represents the angle on the δ band with respect to M, with θ =0 being the Γ -M direction.

a T_c slightly above 40 K [2, 25], especially in samples with large domains that seem to retain intact FeSe layers without Fe vacancies [25]. Alternatively, it is intriguing to investigate whether the ($\text{Li}_{0.8}\text{Fe}_{0.2}$)OH layer plays a role in enhancing T_c . For the monolayer FeSe film on an SrTiO₃ substrate, it was suggested that certain interfacial phonon mode may boost the T_c [12]. However, the phonon-induced replica bands observed in single layer FeSe/STO is not observed here, indicating the electron-phonon interaction strength is much weaker in $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$. This may explains its lower T_c compared with that of the single layer FeSe/STO. Furthermore, as a spacing layer, (Li_{0.8}Fe_{0.2})OH layer may weaken the interlayer coupling between neighboring FeSe layers, which can make the electronic system in FeSe layers more two-dimensional with amplified electronic, magnetic or orbital fluctuation and lead to higher T_c . More studies are demanded for uncovering the physics of superconductivity in (Li_{0.8}Fe_{0.2})OHFeSe as well as other FeSe-derived superconductors.

In summary, we have studied the surface electronic structure of intercalated FeSe-derived superconductor $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$, where there is no Fe-vacancy order or antiferromagnetism in the FeSe layer. Without evidence of other intertwined phase, $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$ offers an excellent platform to study intercalated FeSe-derived superconductors. We found that $(\text{Li}_{0.8}\text{Fe}_{0.2})\text{OHFeSe}$ has a

electronic structure akin to that of $Rb_{0.76}Fe_{1.87}Se_2$, with similar band dispersions and gap symmetry. The higher T_c in $(Li_{0.8}Fe_{0.2})OHFeSe$ could be due to the superior quality of FeSe layer in this material. The $(Li_{0.8}Fe_{0.2})OH$ layer may also play an important role for elevating T_c . Further investigations are required to reveal what is the critical factor that enhances the T_c .

Some of the preliminary data (not shown here) were taken at the beamline 21B1 of National Synchrotron Radiation Research Center(NSRRC), beamline 13U of National Synchrotron Radiation Laboratory (NSRL), and the beamline 5-4 of the Stanford Synchrotron Radiation Light source (SSRL). We gratefully acknowledge the experimental support by Dr. M. Hoesch, Dr. T. Kim, and Dr. P. Dudin at Diamond Light Source, Dr. C. M. Cheng and Prof. K. D. Tsuei at NSRRC, Dr. D. H. Lu and Dr. H. Makoto at SSRL, as well as helpful discussions with J. P. Hu. This work is supported by the National Science Foundation of China and National Basic Research Program of China (973 Program) under Grants No. 2012CB921402, No. 2012CB927401, No. 2011CBA00112, and No. 2011CBA00106. SSRL is operated by the US DOE Office of Basic Energy Science.

Note: upon finishing this work, we noticed another independent ARPES study on (Li_{0.8}Fe_{0.2})OHFeSe, which revealed similar band structure and superconducting gap distribution, by Lin Zhao *et al* posted in arXiv: 1505.06361.

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